Vishay Semiconductors

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Hyperfast Rectifier, 1 A FRED Pt[®]



Cathode O Anode

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS					
I _{F(AV)}	1 A				
V _R	200 V				
V _F at I _F (typ. 125 °C)	0.74 V				
t _{rr}	25 ns				
T _J max.	175 °C				
Package	SMF (DO-219AB)				
Circuit configuration	Single				

FEATURES

- Hyperfast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- · Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage	V _{RRM}		200	V			
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 160 \ ^{\circ}{\rm C} \ ^{(1)}$	1	٨			
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	35	A			
Operating junction and storage temperature range	T _J , T _{Stg}		-65 to +175	°C			

Note

⁽¹⁾ Device on PCB with 8 mm x 16 mm soldering lands

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HALOGEN



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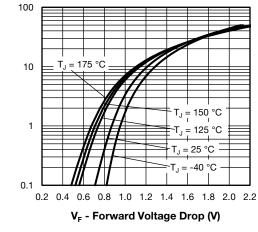
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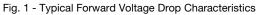
ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Forward voltage	M	I _F = 1 A	-	0.87	0.93	V
	V _F	I _F = 1 A, T _J = 125 °C	-	0.74	0.8	
Reverse leakage current	I _R	V _R = V _R rated	-	-	2	
neverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	0.5	8	μA
Junction capacitance	CT	V _R = 200 V	-	5	-	pF

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
		I _F = 1 A, dI _F /dt = 50 A	õs, V _R = 30 V	-	24	-	
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$	= 0.25 A	-	-	25	ns A
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	
		T _J = 125 °C		-	23	-	
Dook rocovery ourrent	I _{RRM}	T _J = 25 °C	$I_F = 1 A$	-	1.6	-	
Peak recovery current		T _J = 125 °C	dl _F /dt = 200 A/µs V _B = 160 V	-	2.5	-	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	13	-	nC
		T _J = 125 °C		-	30	-	nc

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	+175	°C	
Thermal resistance, junction to mount	R _{thJM}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	17	°C/W	
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	140	°C/W	
Approvimete weight				0.015		g	
Approximate weight				0.0005		oz.	
Marking device		Case style SMF (DO-219AB)		M	DH		







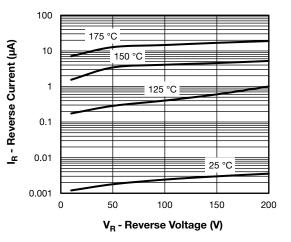


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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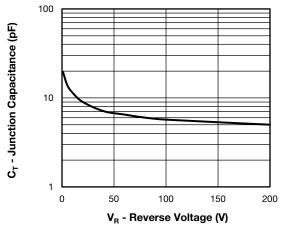
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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

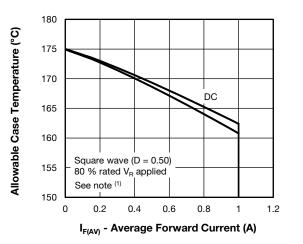


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

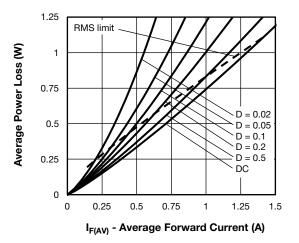
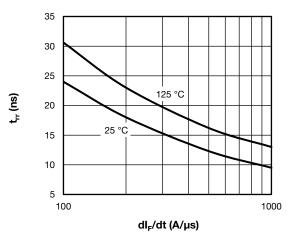


Fig. 5 - Forward Power Loss Characteristics





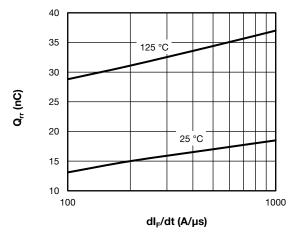


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

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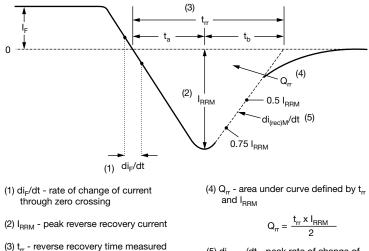
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⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $[\]begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \, \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

VS-1EFH02HM3

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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHA

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Device code	vs-	1	Е	F	н	02	Н	М3
	1	2	3	4	5	6	7	8
	브		-	niconduo	-	oduct		
	2 · 3 ·	- Circ	cuit con	ing (1 = figuratio	,			
	4 -		single o SMF pa					
	5		cess typ	•				
		H =	hyperfa	ast recov	/ery			
	6	- Vol	tage coo	de (02 =	200 V)			
	7 -	- H=	AEC-Q	101 qua	lified			
	8	- M3	= halog	en-free,	RoHS-	complia	ant, and	termina

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-1EFH02HM3/I	10 000	10 000	13"diameter plastic tape and reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95572				
Part marking information	www.vishay.com/doc?95618				
Packaging information	www.vishay.com/doc?95577				
SPICE model	www.vishay.com/doc?96012				

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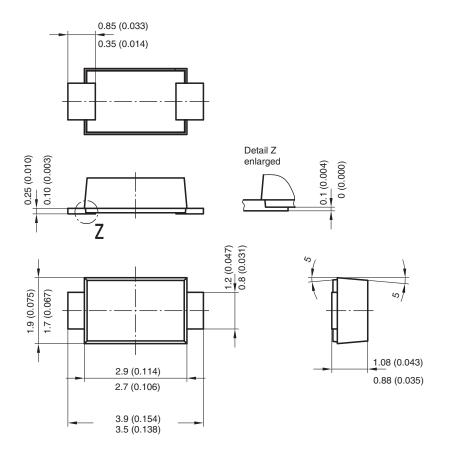
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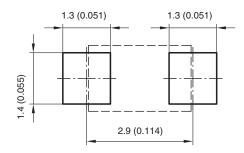
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SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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